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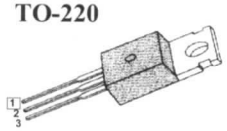
Advanced Power MOSFET — IRFZ44

FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- 175°C Operating Temperature
- Lower Leakage Current: 10μA (Max.) @ V_{DS} = 60V
- Lower $R_{DS(ON)}$: 0.020Ω (Typ.)

BV_{DSS} = 60 V
$R_{DS(on)}$ = 0.024Ω
I_D = 50 A

TO-220



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current (T_C=25°C)	50	A
	Continuous Drain Current (T_C=100°C)	35.4	
I_{DM}	Drain Current-Pulsed (1)	200	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulsed Avalanche Energy (2)	857	mJ
I_{AR}	Avalanche Current (1)	50	A
E_{AR}	Repetitive Avalanche Energy (1)	12.6	mJ
dv/dt	Peak Diode Recovery dv/dt (3)	5.5	V/ns
P_D	Total Power Dissipation (T_C=25°C)	126	W
	Linear Derating Factor	0.84	W/°C
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +175	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8. from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.19	°C/W
$R_{\theta CS}$	Case-to-Sink	0.5	--	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	60	--	--	V	V_{GS}=0V,I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.063	--	V/°C	I_D=250μA ***See Fig 7***
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=5V,I_D=250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=20V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-20V
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	V_{DS}=60V
		--	--	100		V_{DS}=48V,T_C=150°C
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.024	Ω	V_{GS}=10V,I_D=25A (4)
g_{fs}	Forward Transconductance	--	32.6	--	℧	V_{DS}=30V,I_D=25A (4)
C_{iss}	Input Capacitance	--	1770	2300	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz ***See Fig 5***
C_{oss}	Output Capacitance	--	590	680		
C_{rss}	Reverse Transfer Capacitance	--	220	255		
$t_{d(on)}$	Turn-On Delay Time	--	20	40	ns	V_{DD}=30V,I_D=50A, R_G=9.1Ω ***See Fig 13*** (4) (5)
t_r	Rise Time	--	16	40		
$t_{d(off)}$	Turn-Off Delay Time	--	68	140		
t_f	Fall Time	--	70	140		
Q_g	Total Gate Charge	--	64	83	nC	V_{DS}=48V,V_{GS}=10V, I_D=50A ***See Fig 6 & Fig 12*** (4) (5)
Q_{gs}	Gate-Source Charge	--	12.3	--		
Q_{gd}	Gate-Drain (. Miller.) Charge	--	23.6	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	50	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current (1)	--	--	200		
V_{SD}	Diode Forward Voltage (4)	--	--	1.8	V	T_J=25°C,I_S=50A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	85	--	ns	T_J=25°C,I_F=50A
Q_{rr}	Reverse Recovery Charge	--	0.24	--	μC	di_F/dt=100A/μs (4)

Notes;

(1) Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

(2) L=0.4mH, I_{AS}=50A, V_{DD}=25V, R_G=27Ω, Starting T_J=25°C

(3) I_{SD} ≤ 50A, di/dt ≤ 350A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J=25°C

(4) Pulse Test : Pulse Width = 250μs, Duty Cycle ≤ 2%

(5) Essentially Independent of Operating Temperature